



**CHENMKO ENTERPRISE CO.,LTD**

Halogens free devices

**SURFACE MOUNT  
PNP SILICON Transistor**

VOLTAGE 100 Volts CURRENT 5 Ampere

**CHT127ZGP**

**APPLICATION**

- \* Telephony and professional communication equipment.
- \* Other switching applications.

**FEATURE**

- \* Small flat package. ( SC-73/SOT-223 )
- \* Suitable for high packing density.
- \* High saturation current capability.

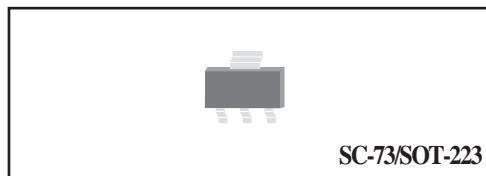
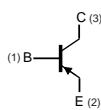
**CONSTRUCTION**

- \* PNP SILICON Transistor

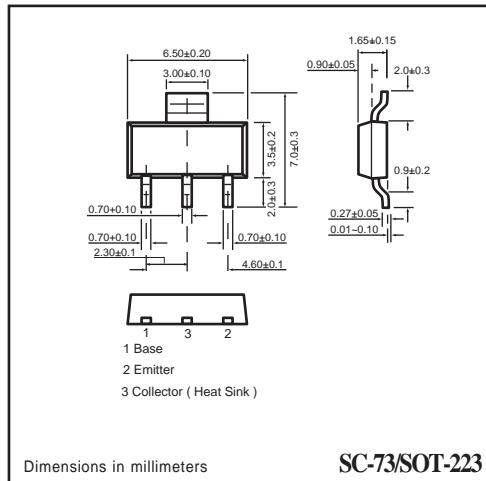
**MARKING**

- \* ZBP

**CIRCUIT**



**SC-73/SOT-223**



**SC-73/SOT-223**

**LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{CBO}$	collector-base voltage	open emitter	—	-100	V
$V_{CEO}$	collector-emitter voltage	open base	—	-100	V
$V_{EBO}$	emitter-base voltage	open collector	—	-5.0	V
$I_C$	collector current (DC)		—	-5.0	A
$I_{CM}$	Peak Collector Current		—	-8.0	A
$P_{tot}$	total power dissipation	$T_{amb} \leq 25^\circ\text{C}$ ; note 1	—	2	W
$T_{stg}$	storage temperature		-65	+150	$^\circ\text{C}$
$T_j$	junction temperature		—	150	$^\circ\text{C}$
$T_{amb}$	operating ambient temperature		-65	+150	$^\circ\text{C}$

**Note**

1. Transistor mounted on an FR4 printed-circuit board.

## RATING CHARACTERISTIC CURVES ( CHT127ZGP )

### CHARACTERISTICS

$T_{amb} = 25^{\circ}\text{C}$  unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$I_{CEO}$	collector cut-off current	$V_{CE} = -50\text{ V}$	—	-500	uA
$I_{CBO}$	collector cut-off current	$V_{CB} = -100\text{ V}$	—	-200	uA
$I_{EBO}$	emitter cut-off current	$V_{EB} = -5.0\text{V}$	—	-2.0	mA
$h_{FE}$	DC current gain	$I_C = -500\text{ mA}; V_{CE} = -3\text{V}$ $I_C = -3.0\text{A}; V_{CE} = -3\text{V}$	1000 1000	— —	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = -3.0\text{ A}; I_B = -12\text{mA}$	—	-2.0	V
		$I_C = -5.0\text{A}; I_B = -20\text{ mA}$	—	-4.0	V
$V_{BEON}$	base-emitter saturation voltage	$I_C = -3.0\text{A}; V_{CE} = -3.0\text{V}$	—	-2.5	V
$C_{ob}$	collector capacitance	$I_E = i_e = 0; V_{CB} = -10\text{ V}; f = 1\text{ MHz}$	—	300	pF
$f_T$	transition frequency	$I_C = -3.0\text{A}; V_{CE} = -4\text{ V}; f = 1.0\text{ MHz}$	4.0	—	MHz